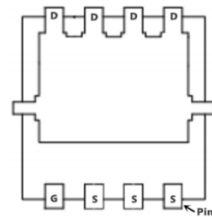
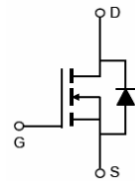


Main Product Characteristics:

V_{DSS}	60V
$R_{DS(on)}$	7.5m Ω (typ.)
I_D	65A


PDFN 5*6-8L

Pin Assignment

Schematic Diagram
Features and Benefits:

- Advanced MOSFET process technology
- Special designed for PWM, load switching and general purpose applications
- Ultra low on-resistance with low gate charge
- Fast switching and reverse body recovery
- 150°C operating temperature


Description:

It utilizes the latest processing techniques to achieve the high cell density and reduces the on-resistance with high repetitive avalanche rating. These features combine to make this design an extremely efficient and reliable device for use in power switching application and a wide variety of other applications.

Absolute max Rating:

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ①	65	A
I_{DM}	Pulsed Drain Current ②	138	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation ③	60	W
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy $L=0.3\text{mH}$	30	mJ
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

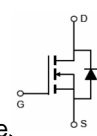
Thermal Resistance

Symbol	Characterizes	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-case ③	—	2.1	$^{\circ}C/W$
$R_{\theta JA}$	Junction-to-ambient ($t \leq 10s$) ④	—	62	$^{\circ}C/W$

Electrical Characterizes @ $T_A=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	60	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	7.5	10	m Ω	$V_{GS}=10V, I_D=20A$
		—	10	13		$V_{GS}=4.5V, I_D=10A$
$V_{GS(th)}$	Gate threshold voltage	1	—	2.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source leakage current	—	—	1	μA	$V_{DS} = 60V, V_{GS} = 0V$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
Q_g	Total gate charge	—	18.2	—	nC	$I_D = 10A,$ $V_{DS}=50V,$ $V_{GS} = 10V$
Q_{gs}	Gate-to-Source charge	—	3.2	—		
Q_{gd}	Gate-to-Drain("Miller") charge	—	3.1	—		
$t_{d(on)}$	Turn-on delay time	—	17.5	—	ns	$V_{GS}=10V, V_{DS}=50V,$ $R_{GEN}=2\Omega$ $I_D = 10A$
t_r	Rise time	—	3.8	—		
$t_{d(off)}$	Turn-Off delay time	—	34.5	—		
t_f	Fall time	—	5.2	—		
C_{iss}	Input capacitance	—	1180	—	pF	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 100kHz$
C_{oss}	Output capacitance	—	199	—		
C_{riss}	Reverse transfer capacitance	—	4	—		

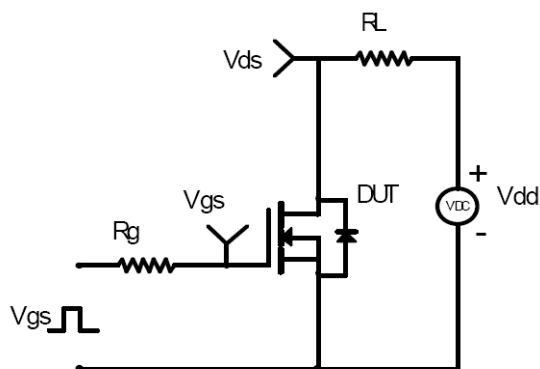
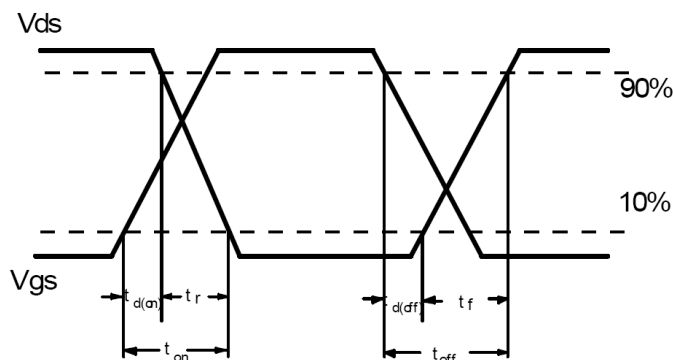
Source-Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	60	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode)	—	—	180	A	
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$I_S=20A, V_{GS}=0V$
t_{rr}	Reverse Recovery Time	—	41	—	ns	$T_J = 25^{\circ}C, I_F = 10A, di/dt = 100A/\mu s$
Q_{rr}	Reverse Recovery Charge	—	36	—	nC	

Test circuits and Waveforms

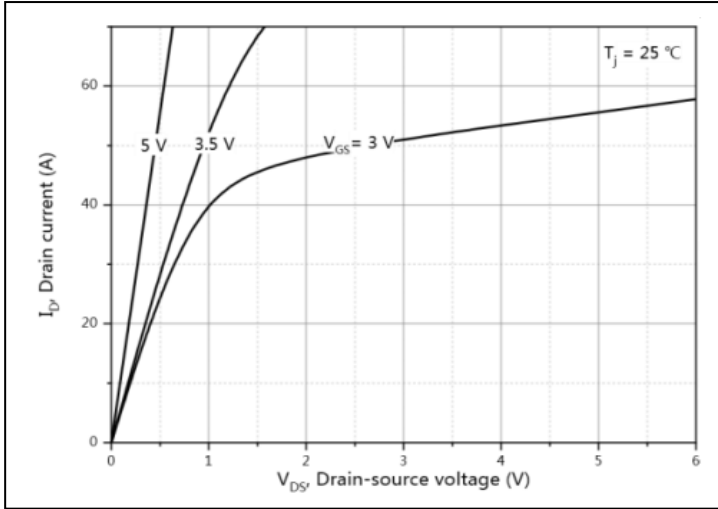
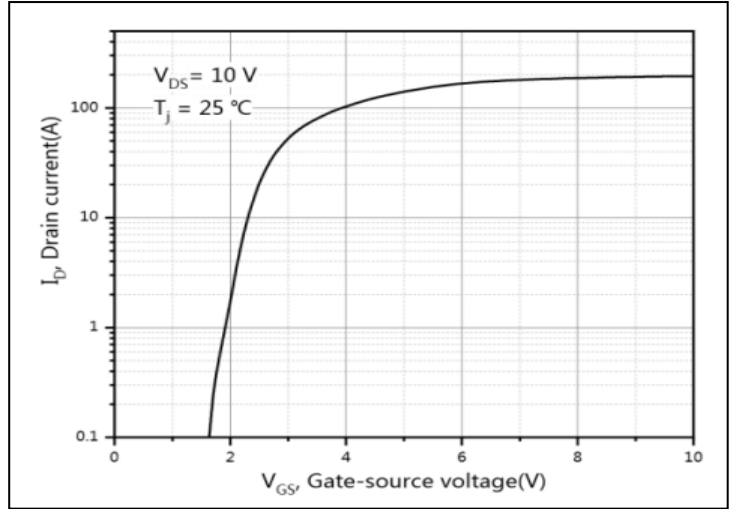
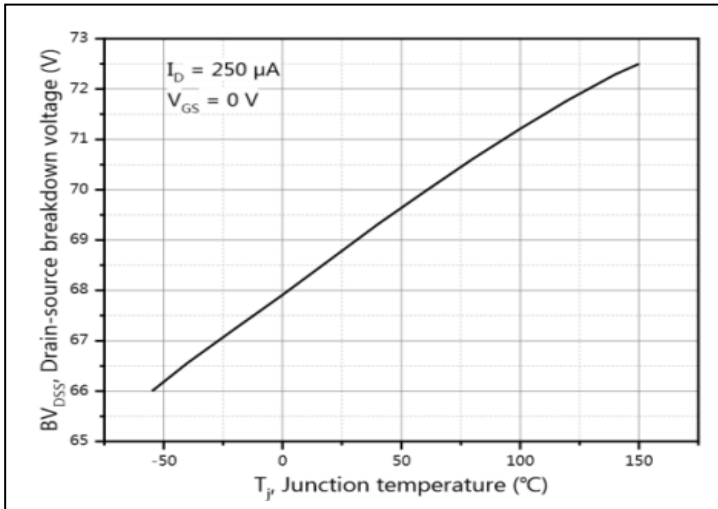
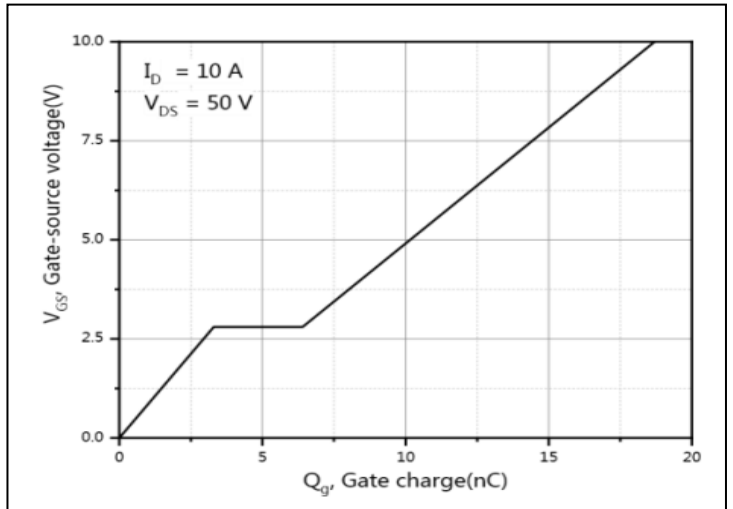
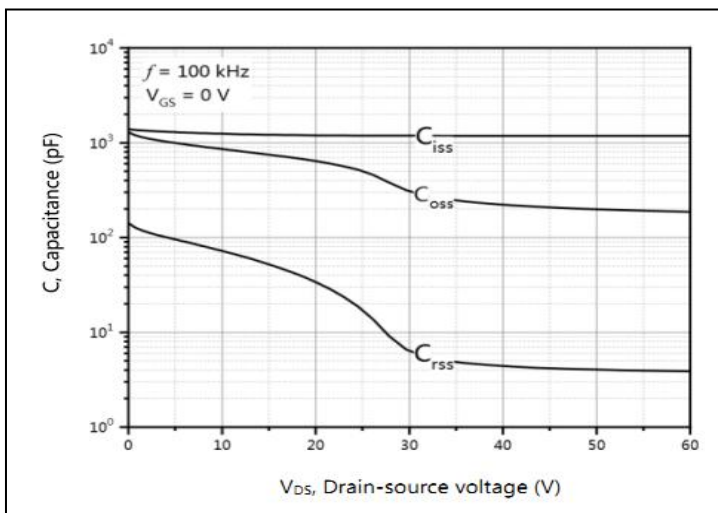
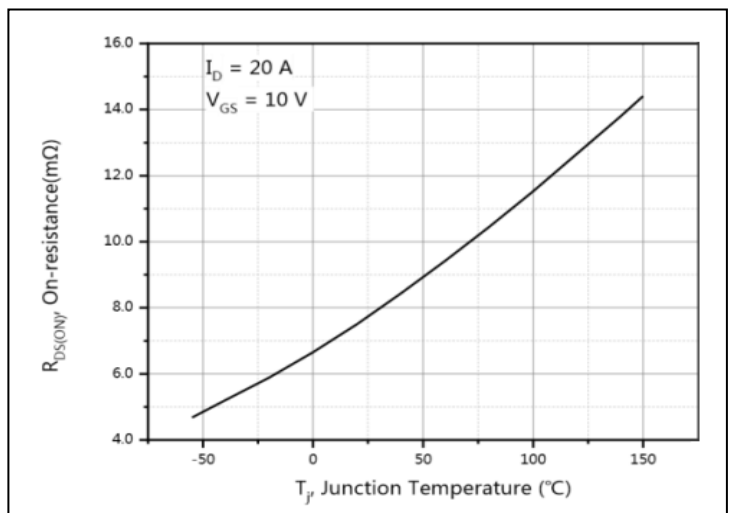
EAS Test Circuit:

Gate charge test circuit:

Switching Time Test Circuit:

Switching Waveforms:


Notes:

- ① Calculated continuous current based on maximum allowable junction temperature.
- ② Repetitive rating; pulse width limited by max. junction temperature.
- ③ The power dissipation PD is based on max. junction temperature, using junction-to-case thermal resistance.
- ④ The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$

Typical electrical and thermal characteristics

Figure 1: Typical Output Characteristics

Figure 2: Transfer Characteristics

Figure 3: Normalized BV_{DS} vs. Junction Temperature

Figure 4: Gate Charge

Figure 5: Capacitance

Figure 6: Normalized On-Resistance vs. Junction Temperature

Typical electrical and thermal characteristics

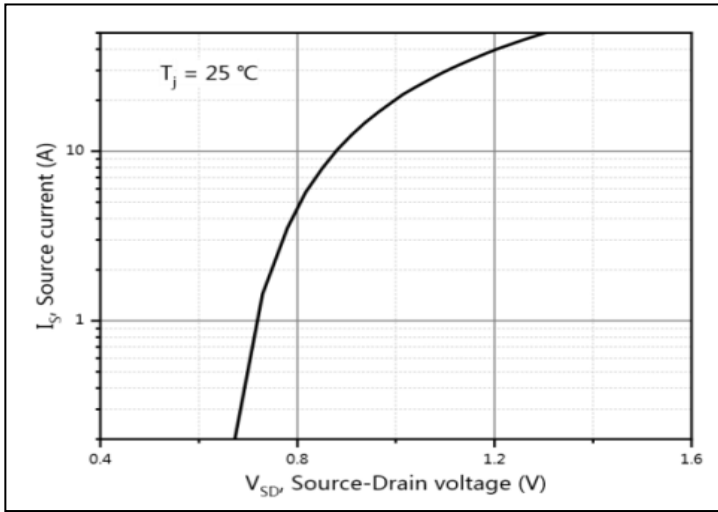


Figure 7: Forward Characteristics of Body Diode

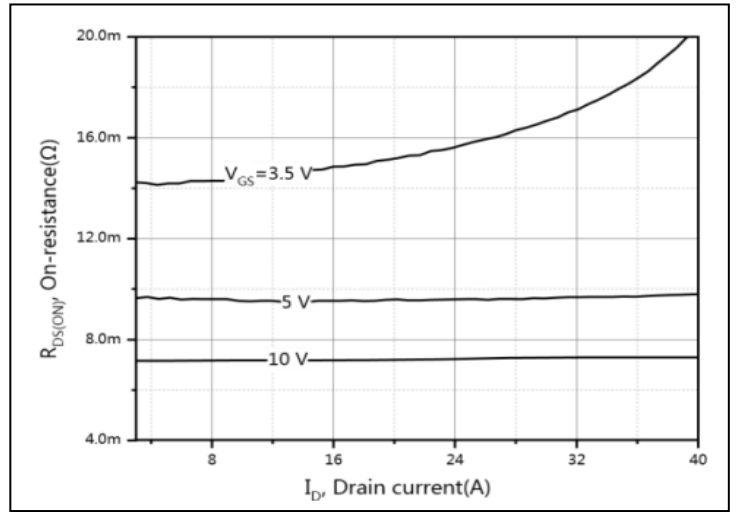


Figure 8: On-Resistance vs. Drain Current

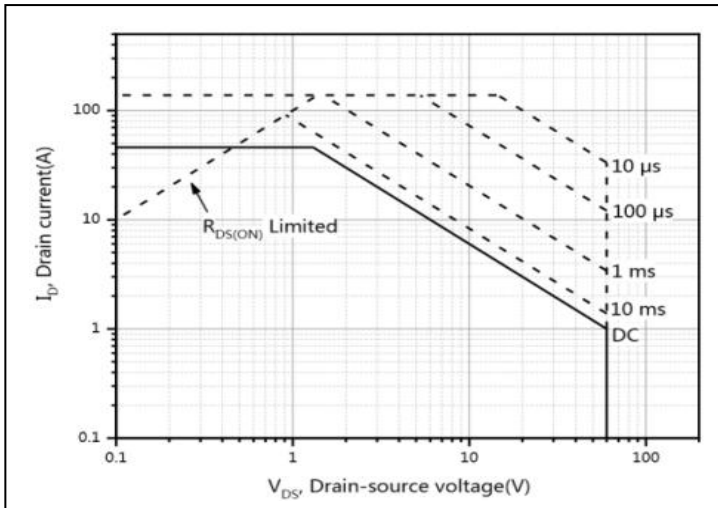
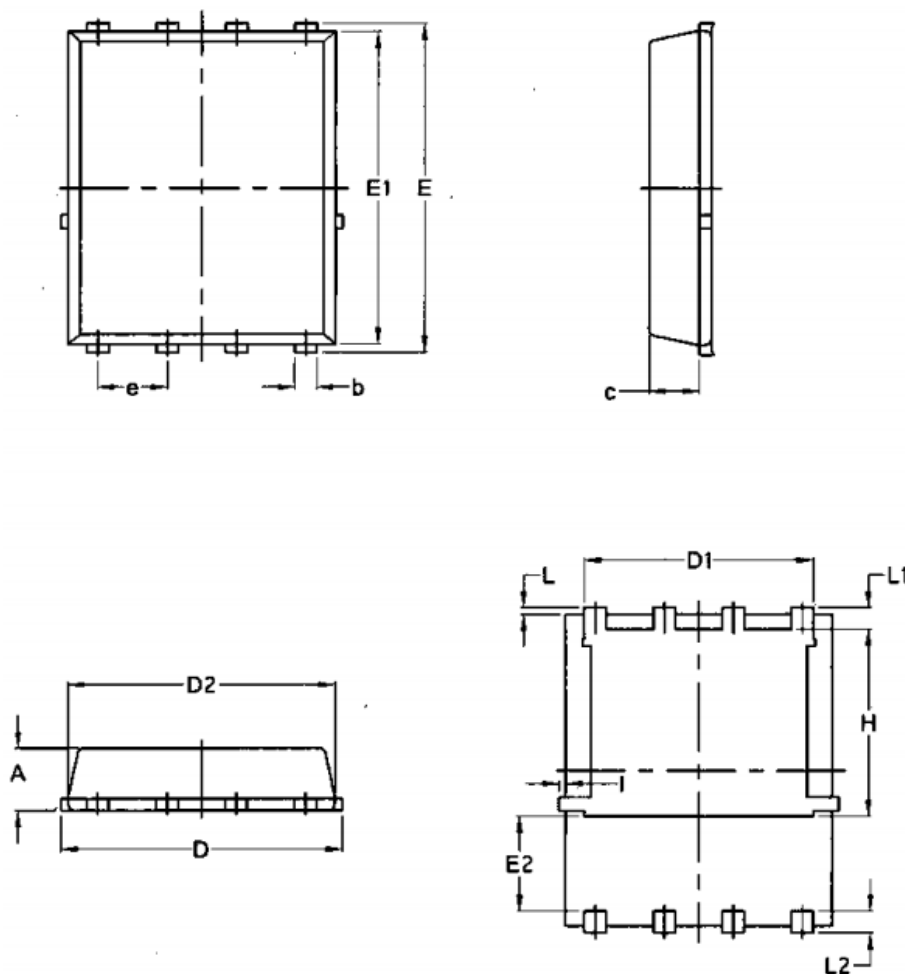


Figure 9: Safe Operation Area

Mechanical Data:


Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070

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